

M. RF Design 분과

Room A
창의관 (106)

일 시 : 2월 16일(목) 11:20-12:35

세션명 : [TA2-M] CMOS RF Device and Circuit Solutions

좌 장 : 박준배(GCT 세미컨덕터), 남일구(부산대학교)

TA2-M-1 11:20-11:50 **[Invited]** Ultra-wideband Design Methodology of CMOS Phase-locked Loops and Voltage-controlled Oscillators

저자: Jae Joon Kim

소속: School of Electrical & Computer Engineering, Ulsan Institute of Science and Technology

TA2-M-2 11:50-12:05 A Capacitive Loaded Low Noise Amplifier for Simultaneous Input Impedance and Minimum Noise Matching

저자: Bum-Kyum Kim¹, Donggu Im¹, and Kwyro Lee^{1,2}

소속: ¹Department of Electrical Engineering, KAIST, ²National NanoFab Center

TA2-M-3 12:05-12:20 DC SOI MOSFET Device Characterization and Optimization Method for Rapid Evaluation of RF Switch Power Handling Capability

저자: Donggu Im¹, Ilhyun Choi², Bum-Kyum Kim¹, Hee-Kyung Bae², Byong-Joo Lee², and Kwyro Lee^{1,2}

소속: ¹Department of Electrical Engineering and Computer Science, KAIST, ²National NanoFab Center

TA2-M-4 12:20-12:35 MOSFET Device Originated Harmonic Distortion Analysis and Optimum Design Methodology for SOI SPDT RF Switch

저자: Donggu Im¹, Bum-Kyum Kim¹, Jaeyoung Choi¹, Youngho Cho², Bonkee Kim², and Kwyro Lee¹

소속: ¹Department of Electrical Engineering and Computer Science, KAIST, ²HiDeep Inc.